

PTO/SB/08A (10-96)  
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 Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>			<b>Complete if Known</b>		
			Application Number	09/730586	
			Filing Date	December 7, 2000	
			First Named Inventor	AVNI, Dror	
			Group Art Unit	unknown 2818	
			Examiner Name	N/A	
			Attorney Docket Number	P-2448-US1	
Sheet	1	of	2		

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Examiner Signature		Date Considered	2/28/02
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<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	unknown <i>09/730,586</i>
				Filing Date	December 7, 2000
				First Named Inventor	AVNI, Dror
				Group Art Unit	unknown <i>2818</i>
				Examiner Name	unknown
				Attorney Docket Number	P-2448-US1
Sheet	2	of	2		

[illegible]

Examiner Signature		Date Considered	2/28/02
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Substitute for form 1449A/PTO				Complete if Known	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary) #4				Application Number	09/730,586
				Filing Date	December 7, 2000
				First Named Inventor	AVNI, Dror
				Group Art Unit	N/A-2818
				Examiner Name	N/A
Sheet	1	of	1	Attorney Docket Number	P-2448-US1

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number of the patent document. Kind of document of the appropriate symbol as indicated on the document under VII. 3. Standard fee is possible. <sup>6</sup> Applicant is to place a check mark here if English language translation is attached.

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
P-2448-US1APPLICATION NO.  
09/730,586SUPPLEMENTAL INFORMATION DISCLOSURE  
STATEMENT BY APPLICANTSAPPLICANTS  
Dror et al.CONFIRMATION NO.  
9625FILING DATE  
December 7, 2000GROUP  
2814

## U.S. PATENT DOCUMENTS

EXAM. INITIAL	DOC. NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)
WJ	3,895,360	07/15/1975	Cricchi et al.			
	4,016,588	04/05/1977	Ohya et al.			
	4,017,888	04/12/1977	Christie et al.			
	4,151,021	04/24/1979	McElroy			
	4,173,766	11/06/1979	Hayes			
	4,173,791	11/06/1979	Bell			
	4,257,832	03/24/1981	Schwabe et al.			
	4,306,353	12/22/1981	Jacobs et al.			
	4,342,149	08/03/1982	Jacobs et al.			
	4,360,900	11/23/1982	Bale			
	4,380,057	04/12/1983	Kotecha et al.			
	4,471,373	09/11/1984	Shimizu et al.			
	4,521,796	06/04/1985	Rajkaran et al.			
	4,527,257	07/02/1985	Cricchi			
	4,630,085	12/16/1986	Koyama			
	4,667,217	05/19/1987	Janning			
	4,742,491	05/03/1988	Liang et al.			
	4,769,340	09/06/1988	Chang et al.			
	4,780,424	10/25/1988	Holler et al.			
	4,847,808	07/11/1989	Kobatake			
	4,870,470	09/26/1989	Bass, Jr. et al.			
	4,941,028	07/10/1990	Chen et al.			
	5,021,999	06/04/1991	Kohda et al.			
	5,075,245	12/24/1991	Woo et al.			
	5,104,819	04/14/1992	Freiberger et al.			
	5,159,570	10/27/1992	Mitchell et al.			
	5,168,334	12/01/1992	Mitchell et al.			
	5,175,120	12/29/1992	Lee			
WJ	5,214,303	05/25/1993	Aoki			

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<i>hns</i>	5,260,593	11/09/1993	Lee			
	5,305,262	04/19/1994	Yoneda			
	5,311,049	05/10/1994	Tsuruta			
	5,324,675	06/28/1994	Hayabuchi			
	5,349,221	09/20/1994	Shimoji			
	5,350,710	09/27/1994	Hong et al.			
	5,359,554	10/25/1994	Odake et al.			
	5,393,701	02/28/1995	Ko et al.			
	5,394,355	02/28/1995	Uramoto et al.			
	5,414,693	05/09/1995	Ma et al.			
	5,418,176	05/23/1995	Yang et al.			
	5,418,743	05/23/1995	Tomioka et al.			
	5,422,844	06/06/1995	Wolstenholme et al.			
	5,424,567	06/13/1995	Chen			
	5,426,605	06/20/1995	Van Berkel et al.			
	5,434,825	07/18/1995	Harari			
	5,436,481	07/25/1995	Egawa et al.			
	5,455,793	10/03/1995	Amin et al.			
	5,467,308	11/14/1995	Chang et al.			
	5,477,499	12/19/1995	Van Buskirk et al.			
	5,496,753	03/05/1996	Sakurai et al.			
	5,518,942	05/21/1996	Shrivasta			
	5,523,251	06/04/1996	Hong			
	5,553,018	09/03/1996	Wang et al.			
	5,599,727	02/04/1997	Hakozaki et al.			
	5,654,568	08/05/1997	Nakao			
	5,656,513	08/12/1997	Wang et al.			
<i>hns</i>	5,712,814	01/27/1998	Fratin et al.			

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EXAM. INITIAL	DOC. NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)
<i>HM</i>	5,726,946	03/10/1998	Yamagata et al.			
	5,751,037	05/12/1998	Aozasa et al.			
	5,760,445	06/02/1998	Diaz			
	5,768,192	06/16/1998	Eitan			
	5,787,036	07/28/1998	Okazawa			
	5,793,079	08/11/1998	Georgescu et al.			
	5,801,076	09/01/1998	Ghneim et al.			
	5,812,449	09/22/1998	Song			
	5,825,686	10/20/1998	Schmitt-Landsiedel			
	5,836,772	11/17/1998	Chang et al.			
	5,841,700	11/24/1998	Chang			
	5,847,441	12/08/1998	Cutler et al.			
<i>HM</i>	5,864,164	01/26/1999	Wen			
	<del>5,870,339</del>	<del>02/09/1999</del>	<del>Khan et al.</del>	<i>Superseded</i>		
<i>HM</i>	5,903,031	05/11/1999	Yamada et al.			
	5,946,558	08/31/1999	Hsu			
	5,963,412	10/05/1999	En			
	5,973,373	10/26/1999	Krautshneider et al.			
	5,991,202	11/23/1999	Derhacopian et al.			
	6,011,725	01/04/2000	Eitan			
	6,018,186	01/25/2000	Hsu			
	6,020,241	02/01/2000	You et al.			
	6,028,324	02/22/2000	Su et al.			
	6,030,871	02/29/2000	Eitan			
	6,034,403	03/07/2000	Wu			
<i>HM</i>	6,034,896	03/07/2000	Ranaweera et al.			

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANTS		APPLICANTS Dror et al.	CONFIRMATION NO. 9625
		FILING DATE December 7, 2000	GROUP 2814

EXAM. INITIAL	DOC. NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)
<i>lha</i>	6,063,666	05/16/2000	Chang et al.			
<i>lha</i>	6,201,282	03/13/2001	Eitan			12/23/1999
<i>lha</i>	<del>08/905,266</del>	<del>07/30/1997</del>	<del>Eitan</del>	<i>duplicate</i>		
<i>lha</i>	09/082,280	05/20/1998	Eitan			
	09/348,720	07/06/1999	Eitan			
	09/413,408	10/06/1999	Eitan			
<i>lha</i>	09/536,125	03/28/2000	Eitan			

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2814

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNT RY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<i>EMO</i>	EP 0751560	06/30/1995					
	EP 1073120	07/13/2000					
	GB 1297899	10/02/1970					
	GB 2157489	03/23/1984					
	JP 05021758	07/12/1991					
	JP 07193151	12/27/1993					
	JP 09162314	12/12/1995					
	WO 81/00790	09/12/1979					
<i>EMV</i>	WO 96/25741	02/16/1995					

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2818

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL	
<u>W</u>	Chan et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," <u>IEEE Electron Device Letters</u> , Vol. EDL-8, No. 3, March 1987.
	Change, J., "Non Volatile Semiconductor Memory Devices," <u>Proceedings of the IEEE</u> , Volume 64 No. 7, issued July 1976.
	Etian et al., "Hot-Electron Injection into the Oxide in n-Channel MOS Devices," <u>IEEE Transactions on Electron Devices</u> , Vol. ED-38, No. 3, pp.328-340, March 1981.
	Glasser et al., "The Design and Analysis of VLSI Circuits," Addison Wesley Publishing Co, Chapter 2, 1988.
	Lee, H., "A New Approach For the Floating-Gate Mos NonVolatile Memory", <u>Applied Physics Letters</u> , Vol. 31, No. 7, pages 475-6, October 1977.
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	Roy, Anariban "Characterization and Modeling of Charge Trapping and Retention in Novel Multi-Dielectric Nonvolatile Semiconductor Memory Device," Doctoral Dissertation, Sherman Fairchild Center, Department of Computer Science and Electrical Engineering, pp. 1-35, 1989.
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	Pickar, K.A., "Ion Implantation in Silicon," <u>Applied Solid State Science</u> , Vol. 5, R. Wolfe Edition, Academic Press, New York, 1975.
<u>W</u>	Bhattacharyya et al., "FET Gate Structure for Nonvolatile N-Channel Read-Mostly Memory Device," <u>IBM Technical Disclosure Bulletin</u> , U.S. IBM Corp. Volume 18, No. 6, page 1768, 1976.

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